

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub- class	Filing Date
Ou	A.	5,541,886 /	07/30/1996	Hasbun	365	230.01	
94	B.	6,046,933	04/04/2000	Nobukata et al.	365	185.03	
ou	C.	6,064,591	05/16/2000	Takeuchi et al.	365	185.03	
194	D.	6,067,248 /	05/23/2000	Yoo	365	185.03	

Foreign Patent or Published Foreign Patent Application

Examiner Initial		Document No.	Publication Date	Country or Patent Office	Class	Sub- Class	Translation Yes No
رصر	E.	EP 0 766 254 A2	04/02/1997	EPO			
	F.						
	G.						

Other Documents

Examiner Initial	No.	Author, Title, Place (e.g. Journal) of Publication, Date
gu	H.	Cho et al., "A Dual-Mode NAND Flash Memory: 1-Gb Multilevel and High-Performance 512-Mb Single-Level Modes," IEEE Journal of Solid-State Circuits, Vol. 36, No. 11, November 2001.
	I.	
	J.	
	K.	
<u> </u>	L.	
	M.	
	N.	
	O.	
Examiner	_	Vule Date Considered 2/20/04

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.